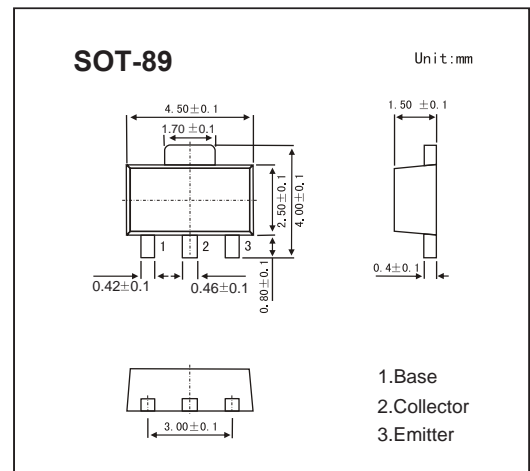


SOT-89 Plastic-Encapsulate Transistors
FEATURES

- High voltage
- High Transition Frequency
- Small Flat Package
- Complementary to KTC4373
- TRANSISTOR (PNP)

MECHANICAL DATA

- Case style:SOT-89 molded plastic
- Mounting position:any


MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V _{CBO}	-120	V
Collector - Emitter Voltage	V _{CEO}	-120	
Emitter - Base Voltage	V _{EBO}	-5	
Collector Current - Continuous	I _C	-800	mA
Base Current	I _B	-160	
Collector Power Dissipation	P _C	500	mW
		1	W
Junction Temperature	T _J	150	°C
Storage Temperature range	T _{stg}	-55 to 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V _{CBO}	I _C = -1mA, I _E =0	-120			V
Collector- emitter breakdown voltage	V _{CEO}	I _C = -10 mA, I _B =0	-120			
Emitter - base breakdown voltage	V _{EBO}	I _E = -1mA, I _C =0	-5			
Collector-base cut-off current	I _{CBO}	V _{CB} = -120 V, I _E =0			-100	nA
Emitter cut-off current	I _{EBO}	V _{EB} = -5V, I _C =0			-100	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =-500 mA, I _B =-50mA			-1	V
Base - emitter saturation voltage	V _{BE(sat)}	I _C = -500 mA, I _B =- 50mA			-1.2	
Base - emitter voltage	V _{BE}	V _{CE} = -5V, I _C = -500mA			-1	
DC current gain	h _{FE}	V _{CE} = -5V, I _C = -100mA	80		240	
Collector output capacitance	C _{ob}	V _{CB} = -10V, I _E =0, f=1MHz			30	pF
Transition frequency	f _T	V _{CE} = -5V, I _C = -100mA		120		MHz

RATINGS AND CHARACTERISTIC CURVES

